

UPS560e3

5 A Schottky Barrier Rectifier

DESCRIPTION

This UPS560e3 in the Powermite3[®] package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3[®] package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

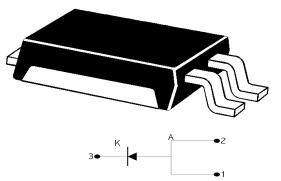
IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)					
Rating	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V		
RMS Reverse Voltage	V _{R (RMS)}	42	V		
Average Rectified Output Current	Ιo	5	А		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T _c =90 °C	I _{FSM}	100	A		
Storage Temperature	T _{STG}	-55 to +150	°C		
Junction Temperature	T_J	-55 to +125	°C		
	AOTEDIC				

THERMAL CHARACTERISTICS

Thermal Resistance					
Junction-to-case (bottom)	R _{eJC}	3.2	°C/ Watt		
Junction to ambient (1)	R _{0JA}	65	°C/ Watt		
(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print					

Powermite 3[™]



Note: 1 Short duration test pulse used to minimize self - heating effect.

KEY FEATURES

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I_{RM}
- Small foot print 190 X 270 mils (1:1 Actual size) See mounting pad details on pg 3

MECHANICAL & PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: \$560.
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel

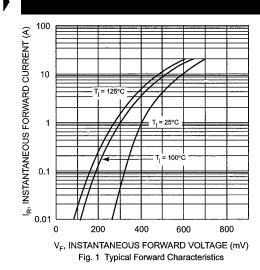
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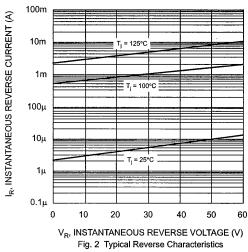


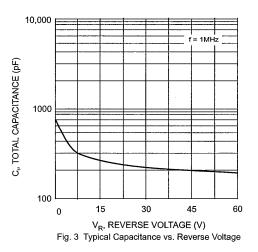
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Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)		I _F = 5 A , T _i = 25 °C		0.65	0.69	
	N/	$I_F = 5 \text{ A}, T_j = 125 \text{ °C}$		0.56	0.60	V
	V _{Fm}	$I_F = 8 A$, $T_j = 25 °C$		0.74	0.78	v
		I _F = 8 A , T _j = 125 °C		0.64	0.68	
Reverse Break Down Voltage						
(Note 1)	V _{BR}	$I_R = 0.2 \text{ mA}$	60			V
Reverse Current (Note1)		V _R = 60 V, T _i = 25°C		2	200	μA
	Im	V _R = 60 V, T _j =125 °C		0.6	20	mA
Capacitance	CT	V _R = 4 V; F = 1 MH _Z		150		pF



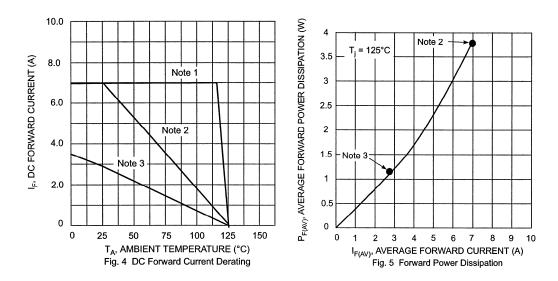




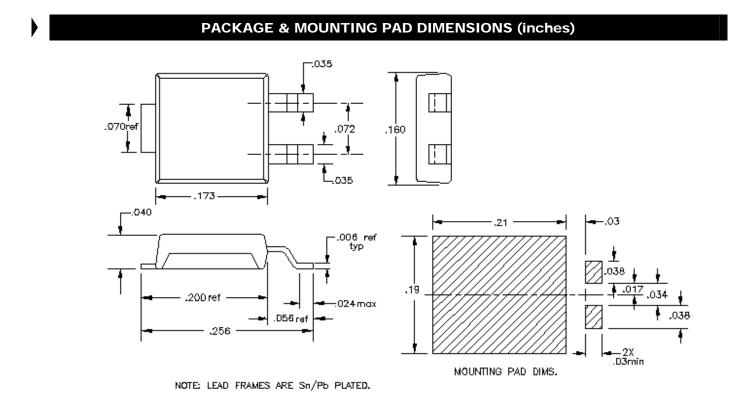


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- NOTE 1: $T_A = T_C$ at case bottom where $R_{\theta JC} = 2.5^{\circ}$ C/W and $R_{\theta CA} = 0^{\circ}$ C/W (infinite heat sink).
- NOTE 2: Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R_{0JA} in range of 20-35° C/W.
- NOTE 3: Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout R_{0JA} in range of 65°C/W. See



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